AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (currently amended): A method of fabricating an aluminum nitride (AlN) substrate for use as a support for electronic components, comprising:

dissolving an oxide precursor in an organic solvent to form a solution, wherein said oxide precursor is an organometallic substance;

dispersing AlN powder in said solution with vigorous agitation to form a suspension;

atomizing said suspension in an inert atmosphere to obtain a powder comprising AlN grains covered with a layer of said oxide precursor; and

spraying [[a]] said powder obtained after atomization onto a support, wherein said ~~powder comprising AlN grains covered with a layer of an~~ oxide precursor ~~chosen from oxide precursors yielding~~ yields an oxide forming a liquid phase around said AlN grains during said spraying[[,]]

~~wherein said substrate obtained by spraying said powder onto said support has a thickness of from 0.1 mm to 0.5 mm~~.

2. (original): The fabrication method claimed in claim 1, wherein said powder is sprayed by means of a plasma torch.

3. (original): The fabrication method claimed in claim 1, wherein said powder is sprayed by means of a flow of air associated with an oxyacetylene torch.

4. (canceled).

5. (previously presented): The fabrication method claimed in claim 1, wherein said oxide is a rare earth oxide.

6. (currently amended): The fabrication method claimed in ~~claim 4~~ claim 1, wherein said oxide precursor is an yttrium oxide precursor, and said powder obtained after atomization comprises an equivalent of 2% to 3% by weight of yttrium oxide.

7. (previously presented): The fabrication method claimed in claim 6, wherein said yttrium oxide precursor is yttrium isopropionate dissolved in propanol.

8. (previously presented): The fabrication method claimed in claim 1, wherein said substrate is obtained by a plurality of passes over said support as a function of required thickness.

9. (previously presented): The fabrication method claimed in claim 1, wherein said support is a metal support and is cooled by jets of compressed air during said step of spraying said powder.

10. (previously presented): The fabrication method claimed in claim 1, wherein said substrate obtained by spraying said powder onto said support is annealed.

11. (canceled).

12. (currently amended): The fabrication method claimed in ~~claim 4~~ claim 1, wherein said AlN powder to be dispersed in said solution with vigorous agitation has a grain diameter on the order of from 2 μm to 3 μm.

13. (currently amended): The fabrication method claimed in ~~claim 4~~ claim 1, wherein said powder obtained by atomizing said suspension in an inert atmosphere comprises hollow spheres having a diameter of from 40 μm to 150 μm.

14. (previously presented): The fabrication method claimed in claim 13, further comprising screening said powder having a diameter of from 40 μm to 150 μm to obtain a powder consisting of hollow spheres having a diameter of from 50 μm to 100 μm.

15. (new): The fabrication method claimed in claim 1, wherein the method comprises, before said spraying, a step of producing on said support an attachment layer to encourage adhesion of said powder to be sprayed.